

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V _{DSS}	60	V
Gate-Source Voltage				V _{GSS}	±20	V
Continuous Drain Current (Note 6)	V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	180 140	mA
Continuous Drain Current (Note 6)	V _{GS} = 5V	Steady State	T _A = +25°C T _A = +70°C	I _D	150 120	mA
Continuous Drain Current (Note 7)	V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	200 160	mA
Continuous Drain Current (Note 7)	V _{GS} = 5V	Steady State	T _A = +25°C T _A = +70°C	I _D	170 140	mA
Pulsed Drain Current (10µs pulse, duty cycle = 1%)				I _{DM}	700	mA

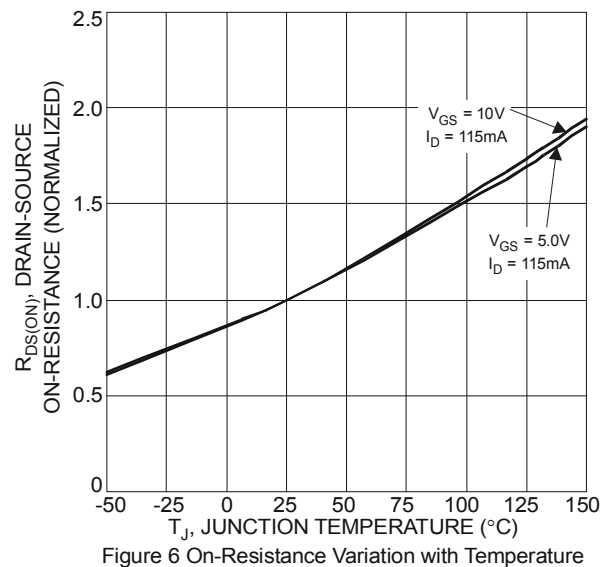
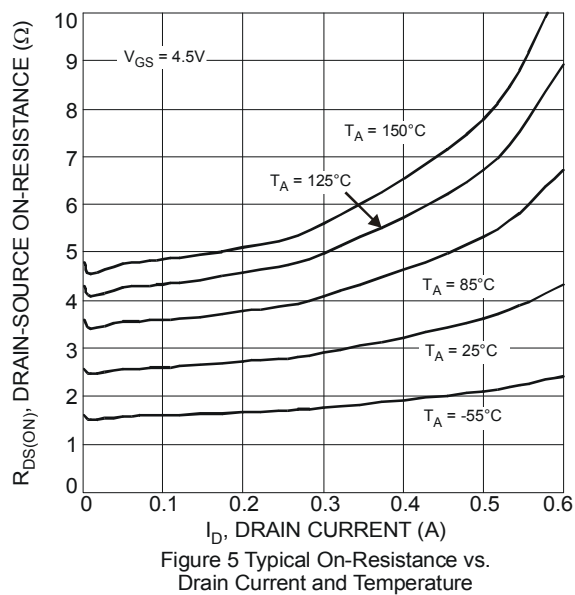
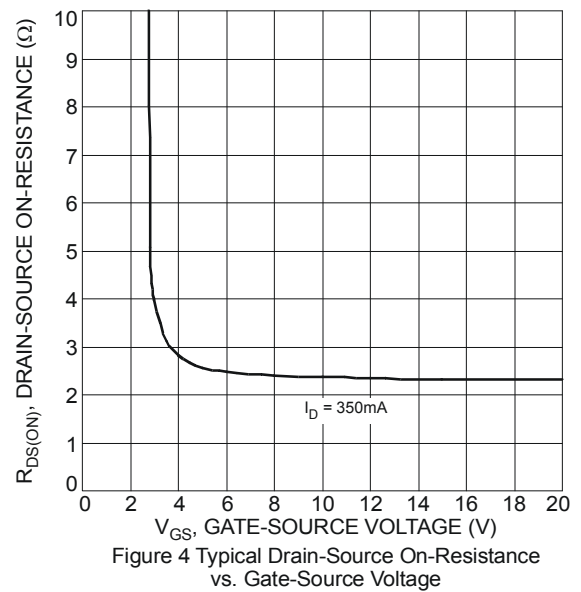
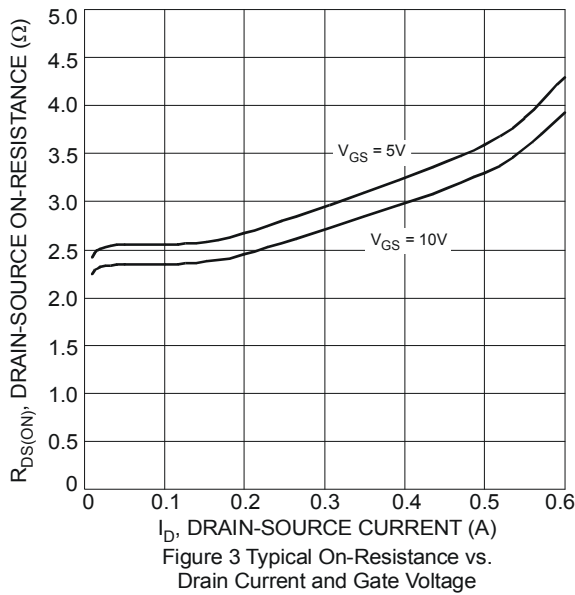
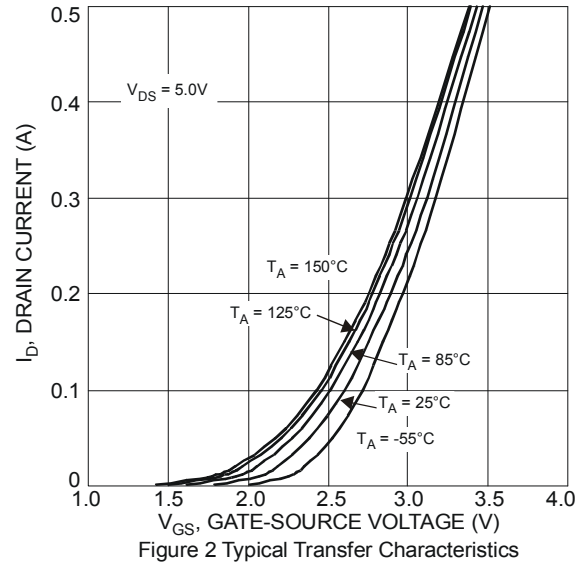
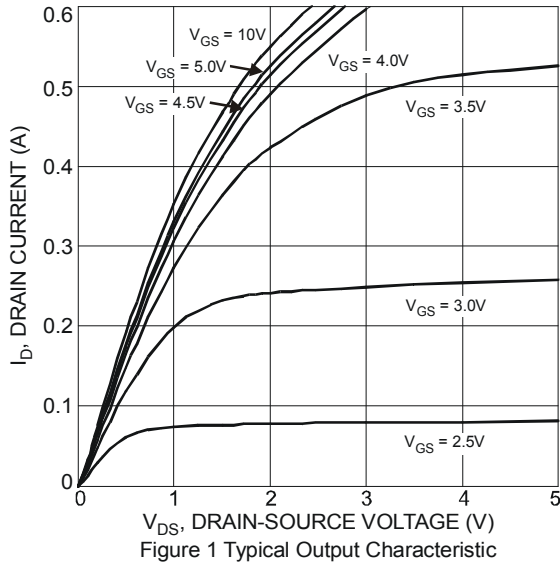
Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	435	°C/W
Total Power Dissipation (Note 7)	P _D	400	mW
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	330	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	139	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	µA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±5	µA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	0.8	—	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	8	Ω	V _{GS} = 5.0V, I _D = 0.115A
		—	—	6	Ω	V _{GS} = 10.0V, I _D = 0.115A
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.115A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	22.0	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	3.2	—		
Reverse Transfer Capacitance	C _{rss}	—	2.0	—		
Gate Resistance	R _G	—	88	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge V _{GS} = 10V	Q _g	—	0.87	—	nC	V _{GS} = 10V, V _{DS} = 30V, I _D = 150mA
Total Gate Charge V _{GS} = 4.5V	Q _g	—	0.43	—		
Gate-Source Charge	Q _{gs}	—	0.11	—		
Gate-Drain Charge	Q _{gd}	—	0.11	—		
Turn-On Delay Time	t _{D(on)}	—	3.3	—	nS	V _{DD} = 30V, I _D = 0.115A, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-On Rise Time	t _r	—	3.2	—		
Turn-Off Delay Time	t _{D(off)}	—	12.0	—		
Turn-Off Fall Time	t _f	—	6.3	—		

- Notes:
6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.



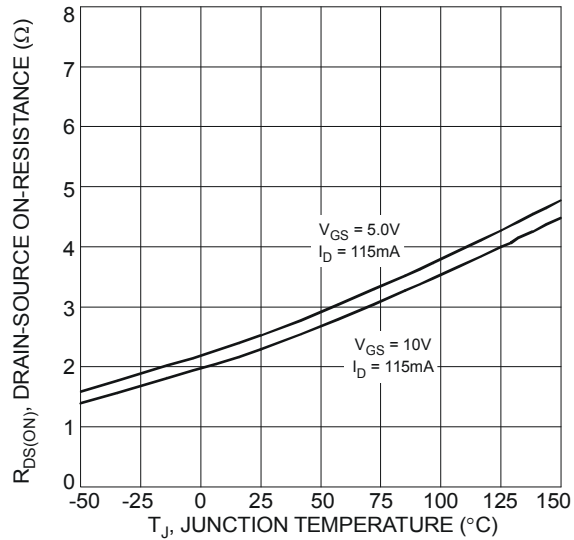


Figure 7 On-Resistance Variation with Temperature

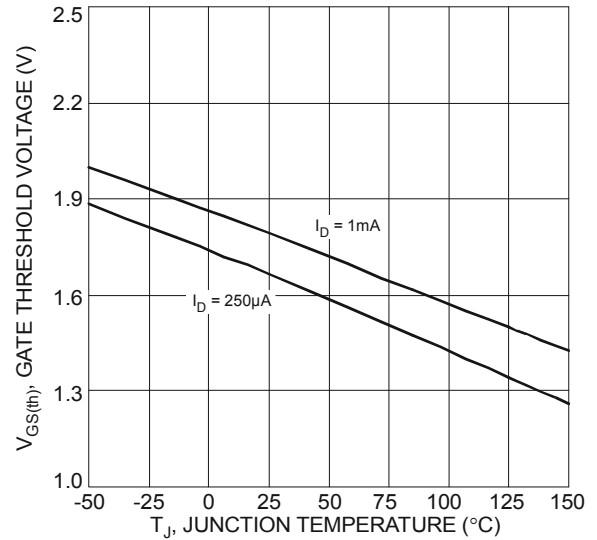


Figure 8 Gate Threshold Variation vs. Ambient Temperature

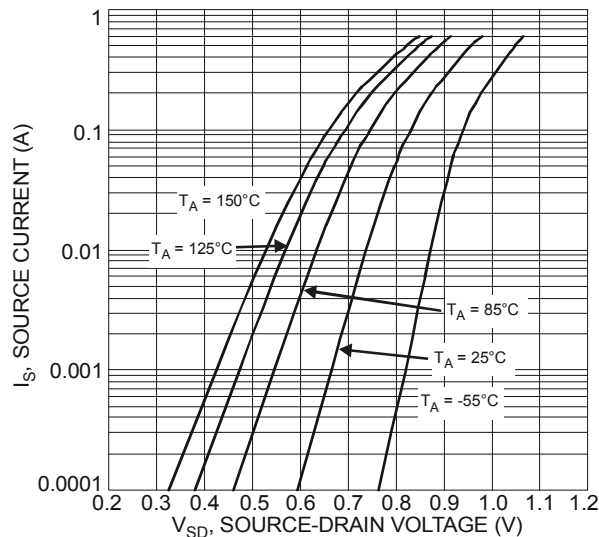


Figure 9 Diode Forward Voltage vs. Current

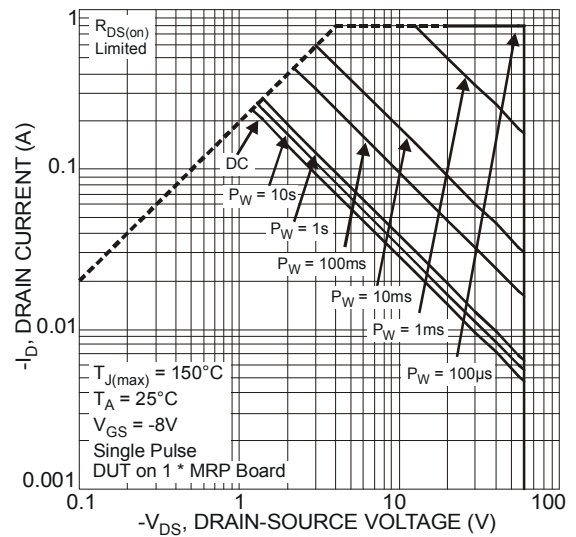
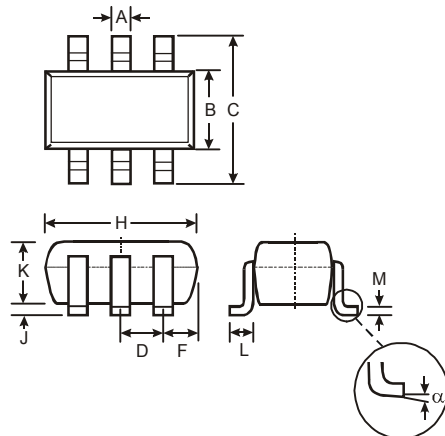


Figure 10 SOA, Safe Operation Area

Package Outline Dimensions

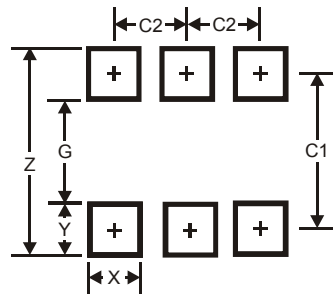
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT363			
Dim	Min	Max	Typ
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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